Product data sheet

1 General description

The BGU8061 is, also known as the BTS3001L, a high-linearity bypass amplifier for wireless infrastructure applications, equipped with fast shutdown to support TDD systems. The LNA has a high input and output return loss and is designed to operate between 0.7 GHz and 1.5 GHz. It is housed in a 3 mm × 3 mm × 0.85 mm 10-terminal plastic thin small outline package. The LNA is ESD protected on all terminals.

2 Features and benefits

- Low-noise performance: NF = 1.1 dB
- High-linearity performance: IP3_O = 36.5 dBm
- High-input return loss > 10 dB
- High-output return loss > 10 dB
- Unconditionally stable up to 20 GHz
- Small 10-terminal leadless package 3 mm × 3 mm × 0.85 mm
- ESD protection on all terminals
- · Moisture sensitivity level 1
- · Fast shut down to support TDD systems
- +5 V single supply

3 Applications

- · Wireless infrastructure
- · Low noise and high-linearity applications
- LTE, W-CDMA, CDMA, GSM
- General-purpose wireless applications
- TDD or FDD systems
- · Suitable for small cells



low-noise high-linearity amplifier

4 Quick reference data

Table 1. Quick reference data

f = 900 MHz; V_{CC} = 5 V; T_{amb} = 25 °C; input and output 50 Ω ; unless otherwise specified. All RF parameters are measured on an application board with the circuit as shown in Figure 29 and components listed in Table 9 implemented. This board is optimized for f = 900 MHz.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CC}	supply current	LNA enable; bypass off	-	70	85	mA
		LNA disable; bypass on	-	3	5	mA
G _{ass}	associated gain	LNA enable; bypass off	19	20.5	22	dB
		LNA disable; bypass on	-1.6	-1.0	-	dB
NF	noise figure	LNA enable; bypass off [1]	-	1.1	1.8	dB
P _{L(1dB)}	output power at 1 dB gain compression	LNA enable; bypass off	19	20.5	-	dBm
IP3 _O	output third-order intercept point	2-tone; tone spacing = 1 MHz; PL =	5 dBn	per ton	ie	
		LNA enable; bypass off	33.5	36.5	-	dBm
		LNA disable; bypass on	-	44	-	dBm

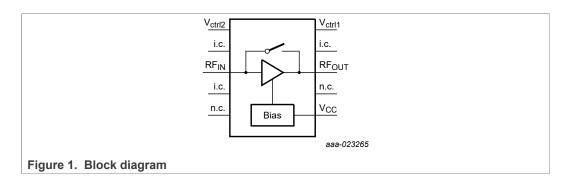
^[1] Connector and Printed-Circuit Board (PCB) losses have been de-embedded.

5 Ordering information

Table 2. Ordering information

Туре	Package				
number	Name	Description	Version		
BGU8061	HVSON10	plastic thermal enhanced very thin small outline package; no leads; 10 terminals; body 3 mm × 3 mm × 0.85 mm	SOT650-2		

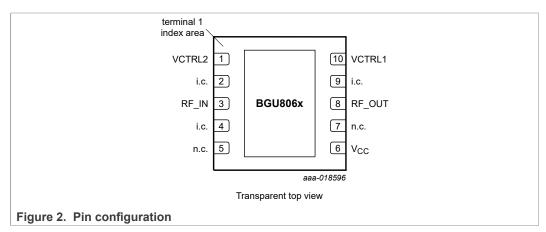
6 Block diagram



low-noise high-linearity amplifier

7 Pinning information

7.1 Pinning



7.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
VCTRL2	1	voltage control 2
i.c.	2, 4, 9	internally connected, can be grounded or left open in the application
RF_IN	3	RF input
n.c.	5	not connected
V _{CC}	6	supply voltage
n.c.	7	not connected
RF_OUT	8	RF output
VCTRL1	10	voltage control 1
GND	exposed die pad	ground

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8 Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-	6	V
V _{i(CTRL1)}	input voltage on pin CTRL1		-	3.6	V
V _{i(CTRL2)}	input voltage on pin CTRL2		-	3.6	V
P _{i(RF)CW}	continuous waveform RF input power		-	20	dBm
T _{amb}	ambient temperature		-40	85	°C
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	150	°C
Р	power dissipation	T _{case} ≤ 125 °C [1]	-	510	mW
V _{ESD}	electrostatic discharge voltage	Human Body Model (HBM) according to ANSI/ESDA/JEDEC standard JS-001-2010	-	2	kV
		Charged Device Model (CDM) according to JEDEC standard 22-C101B	-	1	kV

^[1] Case is ground solder pad

9 Recommended operating conditions

Table 5. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CC}	supply voltage		4.75	5	5.25	V
Z_0	characteristic impedance		-	50	-	Ω

10 Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-case)}	thermal resistance from junction to case	[1] [2]	-	55	-	K/W

^[1] Case is ground solder pad

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^[2] Thermal resistance measured using infrared measurement technique, device mounted on application board and placed in still air

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11 Characteristics

Table 7. Characteristics

f = 900 MHz; V_{CC} = 5 V; T_{amb} = 25 °C; input and output 50 Ω ; unless otherwise specified. All RF parameters are measured on an application board with the circuit as shown in Figure 29 and components listed in Table 9 implemented. This board is optimized for f = 900 MHz.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CC}	supply current	LNA enable; bypass off	-	70	85	mA
		LNA disable; bypass on	-	3	5	mA
G _{ass} associated gain		.NA enable; bypass off 19		20.5	22	dB
		LNA disable; bypass on	-1.6	-1.0	-	dB
G _{flat}	gain flatness	flatness within 100 MHz bandwidth; LNA enable; bypass off				
		700 MHz ≤ f ≤ 1500 MHz	-	0.9	-	dB
		1000 MHz ≤ f ≤ 1500 MHz	-	0.8	-	dB
NF	noise figure	LNA enable; bypass off [1]	-	1.1	1.8	dB
ΔG	gain variation	700 MHz ≤ f ≤ 1500 MHz	-	5.5	-	dB
P _{L(1dB)}	output power at 1 dB gain compression	LNA enable; bypass off	19	20.5	-	dBm
IP3 _O		2-tone; tone spacing = 1 MHz; P _L = 5 dBm per tone				
	intercept point	LNA enable; bypass off	33.5	36.5	-	dBm
		LNA disable; bypass on	-	44	-	dBm
RLin	input return loss	LNA enable; bypass off	-	10	-	dB
		LNA disable; bypass on	-	15	-	dB
RLout	output return loss	LNA enable; bypass off	-	10	-	dB
		LNA disable; bypass on	-	15	-	dB
ISL	isolation	LNA disable; bypass off	-	30	-	dB
		LNA enable; bypass off	-	20	-	dB
t _{s(pon)}	power-on settling time	P _i = -20 dBm	-	0.5	-	μs
t _{s(poff)}	power-off settling time	P _i = -20 dBm	-	0.1	-	μs
K	Rollett stability factor	both on-state and off-state up to f = 20 GHz	1	-	-	-

^[1] Connector and Printed-Circuit Board (PCB) losses have been de-embedded.

low-noise high-linearity amplifier

Table 8. Control truth table

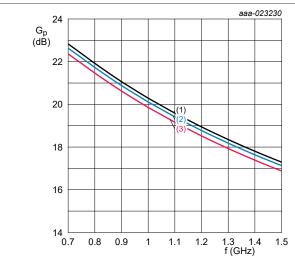
 V_{CC} = 5 V; T_{amb} = 25 °C.

Control signal setting ^[1]		Mode of operation		
CTRL2 (pin 1)	CTRL1 (pin 10)	LNA	bypass	
HIGH	LOW	disable	on	
HIGH	HIGH	disable	on	
LOW	LOW	enable	off	
LOW	HIGH	disable	off	

^[1] A logic LOW is the result of an input voltage on that specific pin between -0.3 V and 0.7 V. A logic HIGH is the result of an input voltage on that specific pin between 1.2 V and 3.6 V.

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12 Graphics



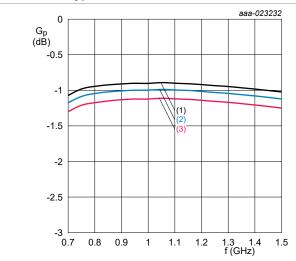
$$V_{CC} = 5 V$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 95 \, ^{\circ}C$$

Figure 3. Power gain as a function of frequency Gain mode; typical values



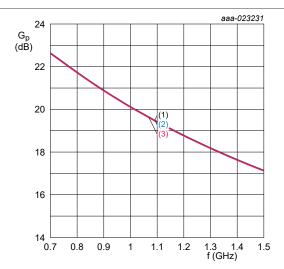
$$V_{CC} = 5 V$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 95 \, ^{\circ}C$$

Figure 5. Power gain as a function of frequency Bypass mode; typical values

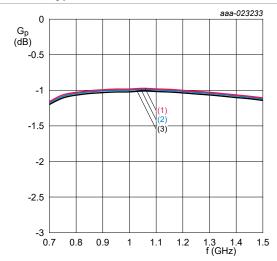


$$(1) V_{CC} = 4.75 V$$

(2)
$$V_{CC} = 5 V$$

$$(3) V_{CC} = 5.25 V$$

Figure 4. Power gain as a function of frequency Gain mode; typical values



$$T_{amb}$$
 = 25 °C

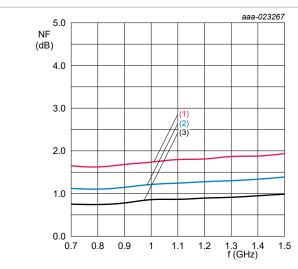
(1)
$$V_{CC} = 4.75 \text{ V}$$

(2)
$$V_{CC} = 5 V$$

$$(3) V_{CC} = 5.25 V$$

Figure 6. Power gain as a function of frequency Bypass mode; typical values

low-noise high-linearity amplifier



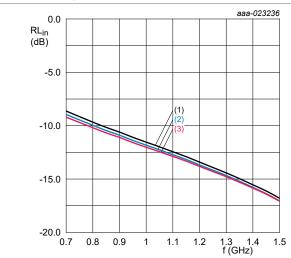
$$V_{CC} = 5 V$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 95 \, ^{\circ}C$$

Figure 7. Noise figure as a function of frequency Gain mode; typical values



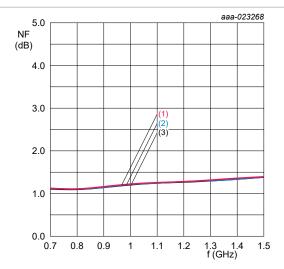
$$V_{CC} = 5 V$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 95 \, ^{\circ}C$$

Figure 9. Input return loss as a function of frequency Gain mode; typical values



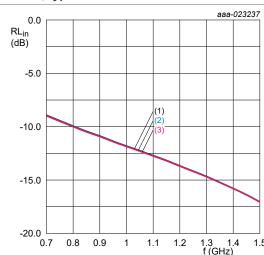
$$T_{amb} = 25 \, ^{\circ}C$$

(1)
$$V_{CC} = 4.75 \text{ V}$$

(2)
$$V_{CC} = 5 V$$

$$(3) V_{CC} = 5.25 V$$

Figure 8. Noise figure as a function of frequency Gain mode; typical values



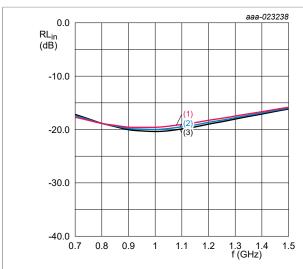
(1)
$$V_{CC} = 4.75 \text{ V}$$

(2)
$$V_{CC} = 5 V$$

$$(3) V_{CC} = 5.25 V$$

Figure 10. Input return loss as a function of frequency Gain mode; typical values

low-noise high-linearity amplifier



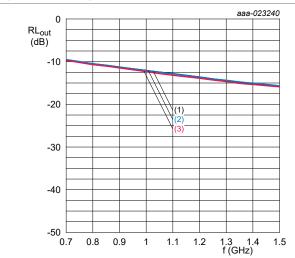
$$V_{CC} = 5 V$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

$$(3) T_{amb} = 95 °C$$

Figure 11. Input return loss as a function of frequency Bypass mode; typical values



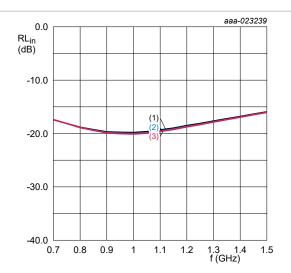
$$V_{CC} = 5 V$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 95 \, ^{\circ}C$$

Figure 13. Output return loss as a function of frequency Gain mode; typical values



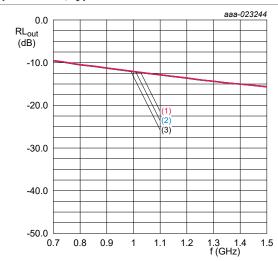
$$T_{amb}$$
 = 25 °C

(1)
$$V_{CC} = 4.75 \text{ V}$$

(2)
$$V_{CC} = 5 V$$

(3)
$$V_{CC} = 5.25 \text{ V}$$

Figure 12. Input return loss as a function of frequency Bypass mode; typical values



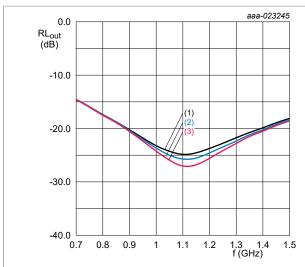
(1)
$$V_{CC} = 4.75 \text{ V}$$

(2)
$$V_{CC} = 5 V$$

$$(3) V_{CC} = 5.25 V$$

Figure 14. Output return loss as a function of frequency Gain mode; typical values

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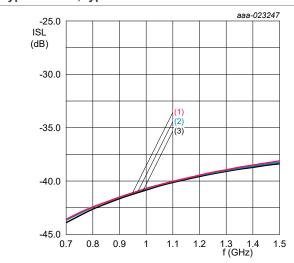
$$V_{CC} = 5 V$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

$$(3) T_{amb} = 95 °C$$

Figure 15. Output return loss as a function of frequency Bypass mode; typical values



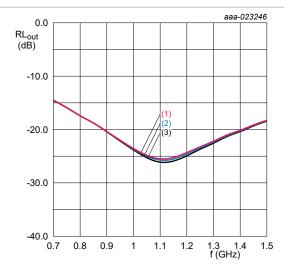
$$V_{CC} = 5 V$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

$$(3) T_{amb} = 95 °C$$

Figure 17. Isolation as a function of frequency Isolation mode; typical values



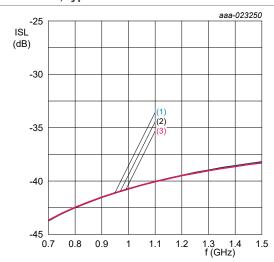
$$T_{amb}$$
 = 25 °C

(1)
$$V_{CC} = 4.75 \text{ V}$$

(2)
$$V_{CC} = 5 V$$

(3)
$$V_{CC} = 5.25 \text{ V}$$

Figure 16. Output return loss as a function of frequency Bypass mode; typical values



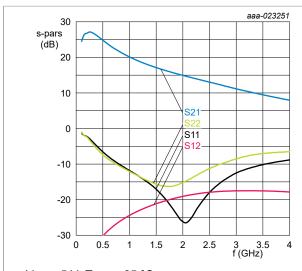
(1)
$$V_{CC} = 4.75 \text{ V}$$

(2)
$$V_{CC} = 5 V$$

$$(3) V_{CC} = 5.25 V$$

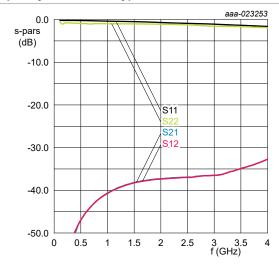
Figure 18. Isolation as a function of frequency Isolation mode; typical values

low-noise high-linearity amplifier



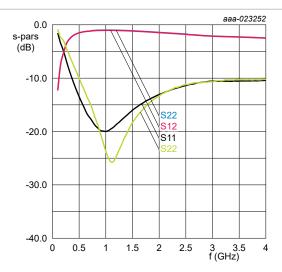
 V_{CC} = 5 V; T_{amb} = 25 °C

Figure 19. Wideband S-parameters as function of frequency Gain mode; typical values



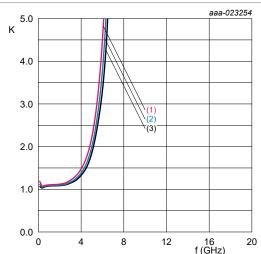
 V_{CC} = 5 V; T_{amb} = 25 °C

Figure 21. Wideband S-parameters as function of frequency Isolation mode; typical values



 V_{CC} = 5 V; T_{amb} = 25 °C

Figure 20. Wideband S-parameters as function of frequency Bypass mode; typical values



 $V_{CC} = 5 V$

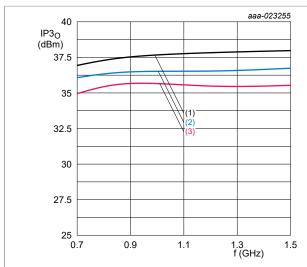
(1) $T_{amb} = -40 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

 $(3) T_{amb} = 95 °C$

Figure 22. Rollett stability factor as function of frequency Gain mode; typical values

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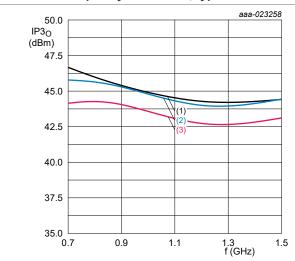


$$V_{CC} = 5 V$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(3)
$$T_{amb} = 95 \, ^{\circ}C$$

Figure 23. Output third-order intercept point as a function of frequency Gain mode; typical values



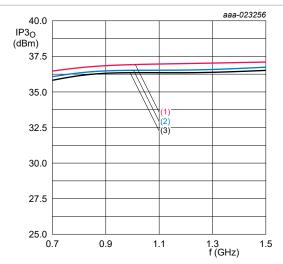
$$V_{CC} = 5 V$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

$$(3) T_{amb} = 95 °C$$

Figure 25. Output third-order intercept point as a function of frequency Bypass mode; typical values

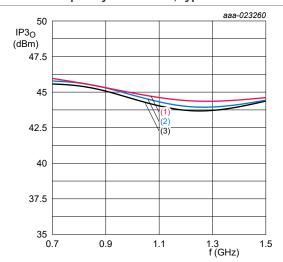


(1)
$$V_{CC} = 4.75 \text{ V}$$

(2)
$$V_{CC} = 5 V$$

(3)
$$V_{CC} = 5.25 \text{ V}$$

Figure 24. Output third-order intercept point as a function of frequency Gain mode; typical values



(1)
$$V_{CC} = 4.75 \text{ V}$$

(2)
$$V_{CC} = 5 V$$

$$(3) V_{CC} = 5.25 V$$

Figure 26. Output third-order intercept point as a function of frequency Bypass mode; typical values

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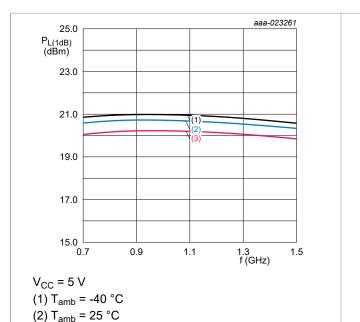
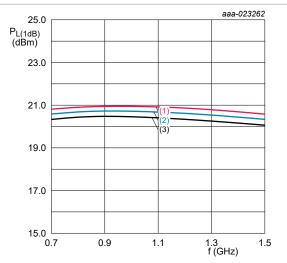


Figure 27. Output power at 1 dB gain compression as a function of frequency Gain mode; typical values

(3) $T_{amb} = 95 \, ^{\circ}C$



(1)
$$V_{CC} = 4.75 \text{ V}$$

(2)
$$V_{CC} = 5 V$$

$$(3) V_{CC} = 5.25 V$$

Figure 28. Output power at 1 dB gain compression as a function of frequency Gain mode; typical values

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13 Application information

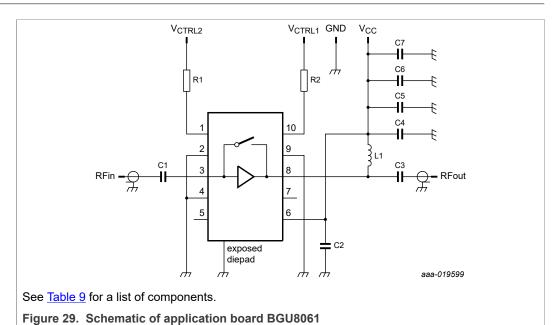
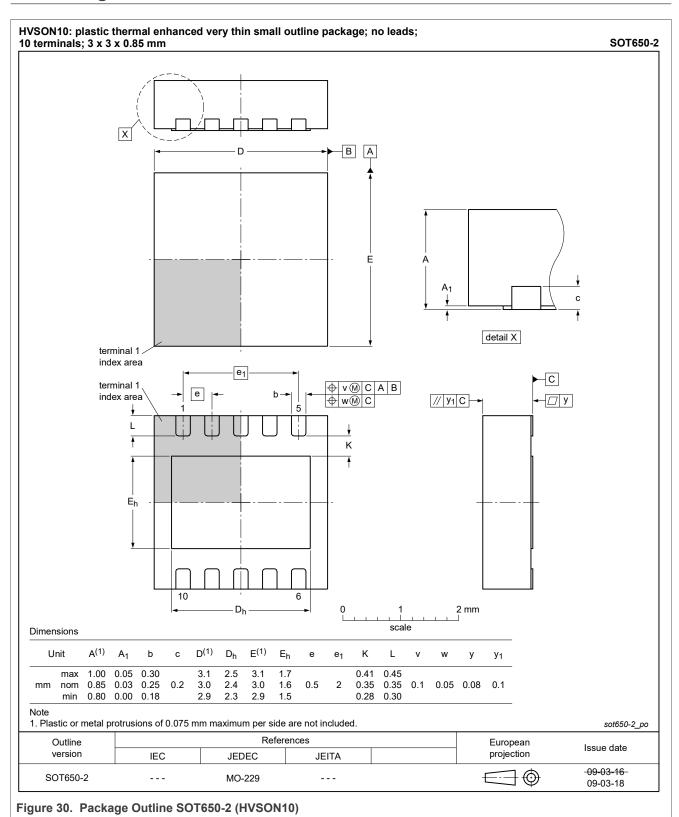


Table 9. List of components See Figure 29 for schematics.

Component	Description	Value	Remarks
C1	capacitor	100 nF	
C2, C3	capacitor	100 pF	
C4	capacitor	1 nF	
C5	capacitor	-	optional
C6	capacitor	10 nF	
C7	capacitor	1 μF	
L1	inductor	15 nH	
R1, R2	resistor	1 kΩ	

low-noise high-linearity amplifier

14 Package outline



BGU8061

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low-noise high-linearity amplifier

15 Abbreviations

Table 10. Abbreviations

Acronym	Description	
CDMA	code division multiple access	
ESD	electrostatic discharge	
FDD	requency-division duplexing	
GSM	lobal system for mobile communication	
LNA	ow noise amplifier	
LTE	long-term evolution	
TDD	time-division duplexing	
W-CDMA	wideband code division multiple access	

16 Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
BGU8061 v.2.1	20220323	product data sheet	2022030221	BGU8061 v.2		
Modifications		added legal information adapted the data sheet to the latest NXP rules(no data is changed)				
BGU8061 v.2	20170127	product data sheet	-	BGU8061 v.1		
Modifications	added BTS3001L a	added BTS3001L according to our new naming convention				
BGU8061 v.1	<tbd></tbd>	product data sheet	-	-		

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17 Legal information

17.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL https://www.nxp.com.

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